

L Number	Hits	Search Text	DB	Time stamp
1	346691	wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:42
2	9070	removing near photoresist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:42
3	3622	wafer and (removing near photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:42
4	20550	process near chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:42
5	18592	wafer near (stage or support)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:43
6	186	(wafer and (removing near photoresist)) and (process near chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:43
7	38	(wafer near (stage or support)) and ((wafer and (removing near photoresist)) and (process near chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:43
9	0	((wafer near (stage or support)) and ((wafer and (removing near photoresist)) and (process near chamber))) and (heating near temperature near "210")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:43
8	12	heating near temperature near "210"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:45
10	104398	heating near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:45
11	0	((wafer near (stage or support)) and ((wafer and (removing near photoresist)) and (process near chamber))) and (heating near temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:45
12	6204	wafer and (heating near temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:45
13	123	(removing near photoresist) and (wafer and (heating near temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:45

14	5	(process near chamber) and ((removing near photoresist) and (wafer and (heating near temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:56
15	382588	plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:56
16	74	((removing near photoresist) and (wafer and (heating near temperature))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:57
17	117296	219/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:57
18	1	((removing near photoresist) and (wafer and (heating near temperature))) and plasma) and 219/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 17:59
19	21	wafer and (removing near photoresist) and plasma and 219/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 18:01
20	927645	heating and temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 18:01
21	14	(wafer and (removing near photoresist) and plasma and 219/\$.ccls.) and (heating and temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/03 18:01